

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New **Divisional** Application of:)
Shunpei YAMAZAKI et al.) Art Unit: 2811
Based on U.S. Serial No. 09/848,307) Examiner: S. Hu
Filed on: May 4, 2001)
For: SEMICONDUCTOR DEVICE AND METHOD)
OF FABRICATING THE SAME) Date: July 31, 2001



S. Hu
#2
10-32-01

INFORMATION DISCLOSURE STATEMENT
AND NOTIFICATION OF RELATED APPLICATIONS

Commissioner for Patents
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the reference(s) listed on the attached Form PTO-1449 be made of record in the above-identified application.

The references listed on the attached Form PTO-1449 were cited in parent application Serial Nos. 09/848,307; 09/334,645; 08/821,656; 08/486,218 and 08/195,713.

Respectfully Submitted,

Jeffrey L. Costellia
Registration No. 35,483

Nixon Peabody LLP
8180 Greensboro Drive, Suite 800
McLean, Virginia 22102
(703) 790-9110

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Atty D cket 0756-2345

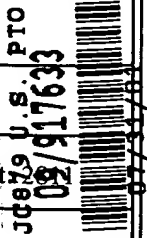
Serial No. N/A

INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 31, 2001

Group Art Unit



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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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